

EAST - U0677350.wsp:1

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BB-1 ISBAT IS-BRBLIS FRO-190 IBM TDE

Color photograph by SP

R. Prudha

#### **8. Highlight all big terms initially**

((vertical adj transistor) and (plug with (dielectric or insulat\$4))) not ((vertical adj transistor) and (monocrystalline adj silicon) and (plug with (dielectric or insulat\$4)))) and (monocrystalline)

	U	I	PT	P	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	R	Inventor	S	C
1	■	■	■	■	US 6207977	20010327	63	Vertical MISFET devices	257/192	257/19; 257/194; 257/331;	■	Augusto, Carlos Jorge Ramiro Proenca	■	■
2	■	■	■	■	US 5963800	19991005	60	CMOS integration process having vertical channel	438/212	257/334; 257/E21.643; 257/E27.062;	■	Augusto, Carlos Jorge Ramiro Proenca	■	■
3	■	■	■	■	US 5920088	19990706	61	Vertical MISFET devices	257/192	257/194; 257/330; 257/E21.643;	■	Augusto, Carlos Jorge Ramiro Proenca	■	■
4	■	■	■	■	US 5914504	19990622	60	DRAM applications using vertical MISFET devices	257/192	257/195; 257/200; 257/201;	■	Augusto, Carlos Jorge Ramiro Proenca	■	■
5	■	■	■	■	US 5010386	19910423	8	Insulator separated vertical CMOS	257/369	257/328; 257/633; 257/E27.062	■	Groover, III, Robert	■	■